## Mariusz Ciorga

List of Publications by Year in descending order

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1040056 1125743 13 338 9 13 citations h-index g-index papers 13 13 13 401 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Electrical spin injection and detection in lateral all-semiconductor devices. Physical Review B, 2009, 79, .	3.2	120
2	Electrical Spin Injection into High Mobility 2D Systems. Physical Review Letters, 2014, 113, 236602.	7.8	37
3	Allâ <b>€e</b> lectrical detection of spin Hall effect in semiconductors. Physica Status Solidi (B): Basic Research, 2014, 251, 1725-1735.	1.5	32
4	Shot Noise Induced by Nonequilibrium Spin Accumulation. Physical Review Letters, 2015, 114, 016601.	7.8	28
5	Gate-tunable large magnetoresistance in an all-semiconductor spin valve device. Nature Communications, 2017, 8, 1807.	12.8	27
6	Annealing-induced magnetic moments detected by spin precession measurements in epitaxial graphene on SiC. Physical Review B, 2013, 87, .	3.2	24
7	Dynamic nuclear spin polarization in an all-semiconductor spin injection device with (Ga,Mn)As/ <i>n</i> -GaAs spin Esaki diode. Applied Physics Letters, 2012, 101, .	3.3	22
8	Giant enhancement of spin detection sensitivity in (Ga,Mn)As/GaAs Esaki diodes. Physical Review B, 2014, 89, .	3.2	20
9	All-electrical measurements of direct spin Hall effect in GaAs with Esaki diode electrodes. Physical Review B, 2012, 86, .	3.2	13
10	Electrical spin injection and detection in high mobility 2DEG systems. Journal of Physics Condensed Matter, 2016, 28, 453003.	1.8	7
11	In-plane tunneling anisotropic magnetoresistance in (Ga,Mn)As/GaAs Esaki diodes in the regime of the excess current. Applied Physics Letters, 2015, 106, 262402.	3.3	5
12	Tunneling mechanism in a (Ga,Mn)As/GaAs-based spin Esaki diode investigated by bias-dependent shot noise measurements. Physical Review B, 2020, 102, .	3.2	2
13	Spatial variation of dynamic nuclear spin polarization probed by the non-local Hanle effect. Applied Physics Letters, 2018, 112, 132403.	3.3	1